

09501307-070901

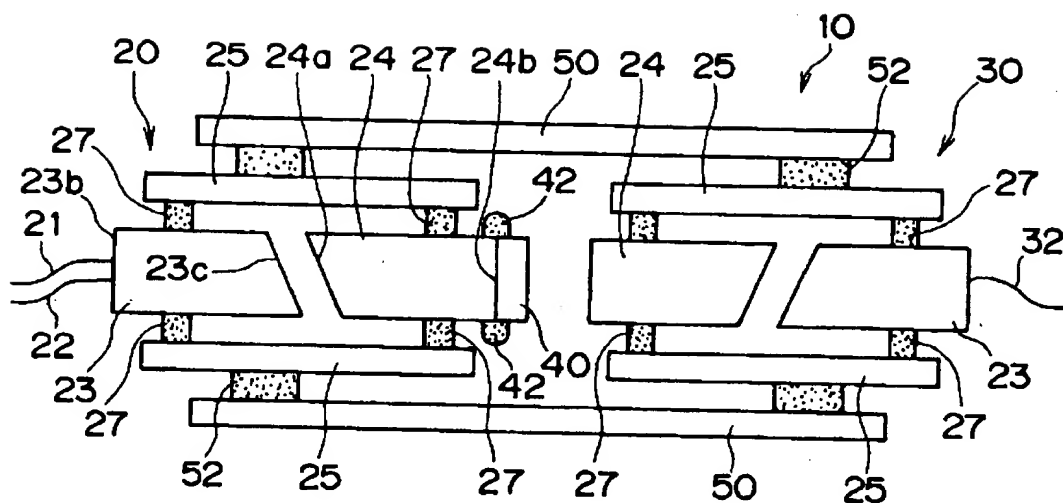


FIG. 1

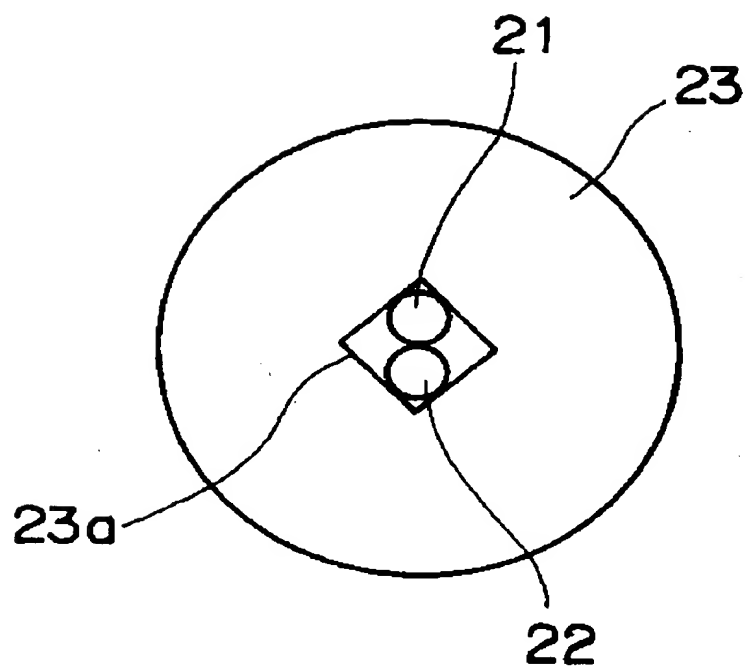


FIG. 2

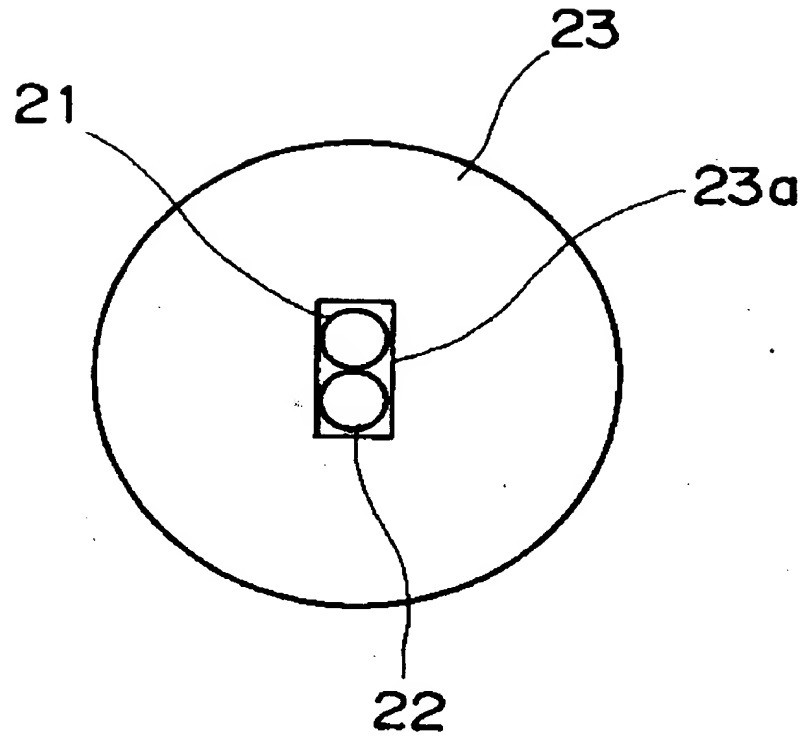


FIG. 3

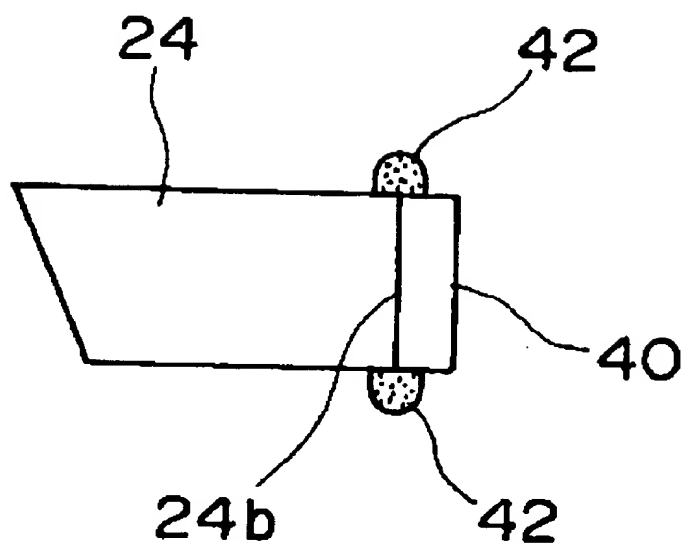
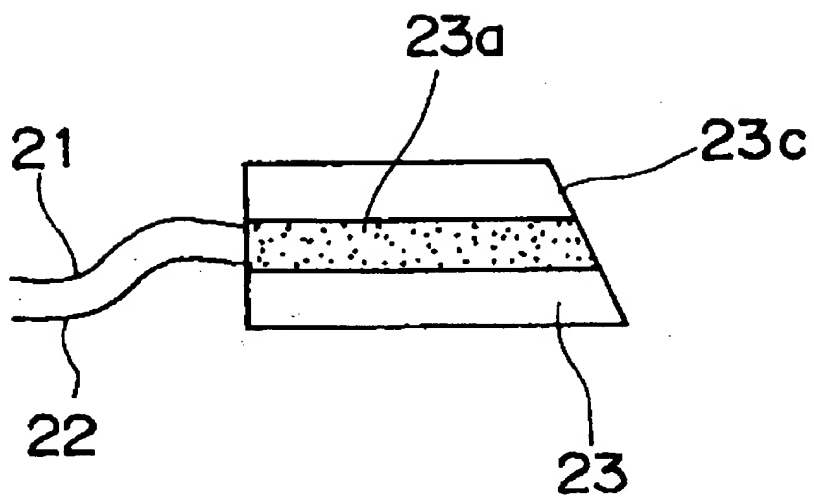


FIG. 4



F I G . 5

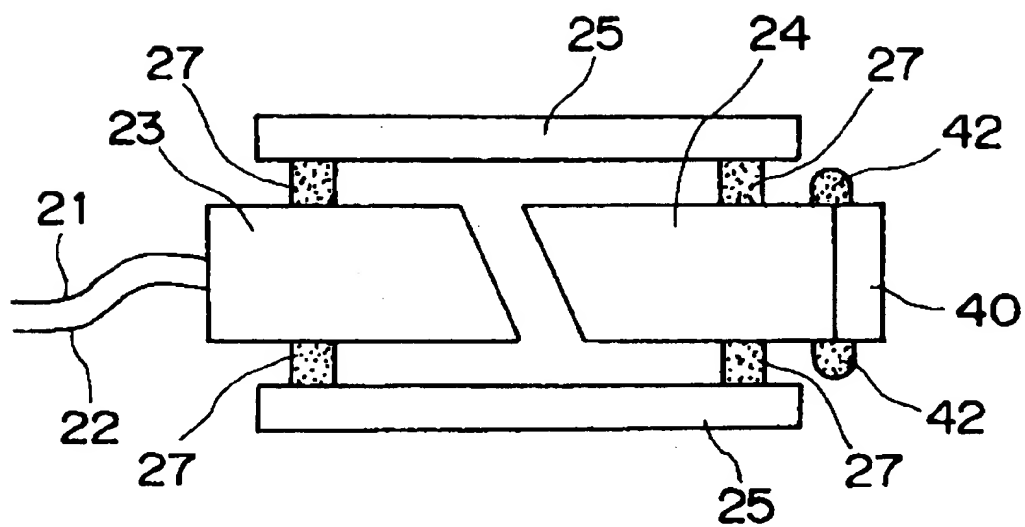


FIG. 6

0904307.070904
T06020 20ET0660

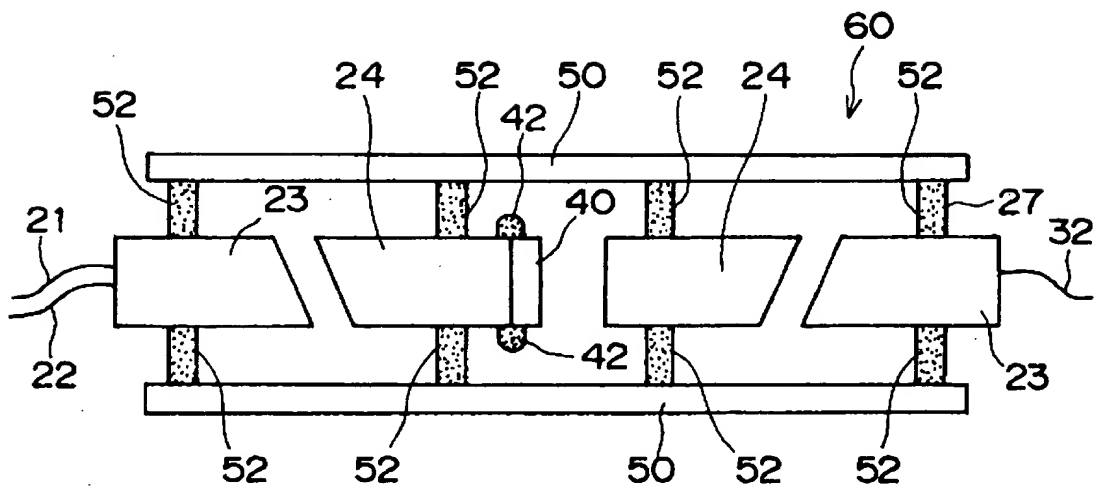


FIG. 7

09501307.070901
106020 20E10660

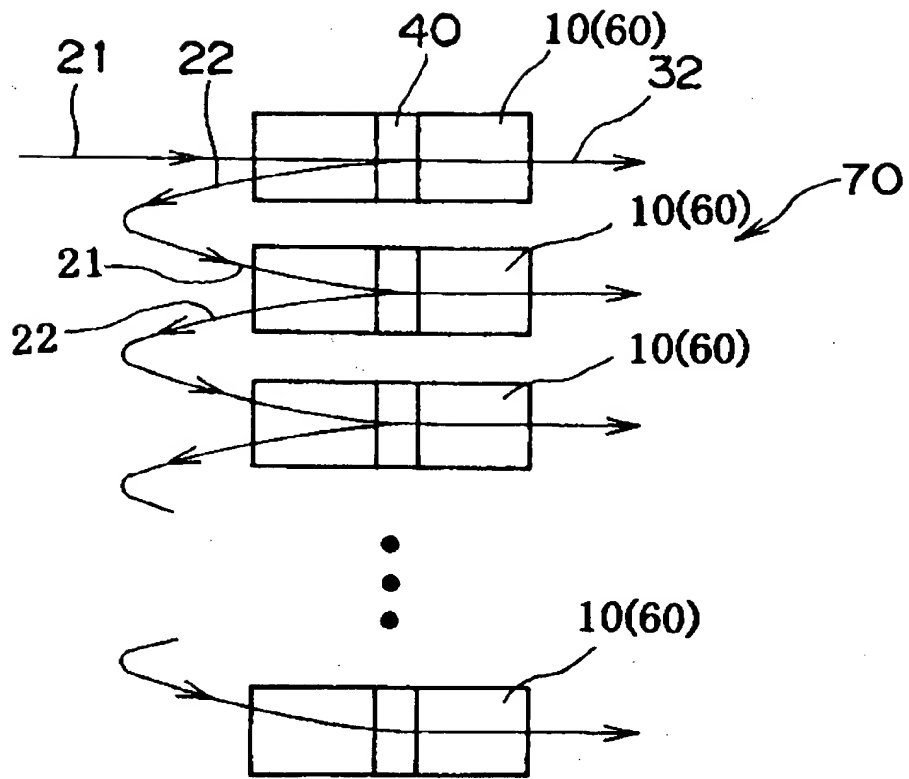


FIG. 8

09001307 070904
T06020 20ET00660

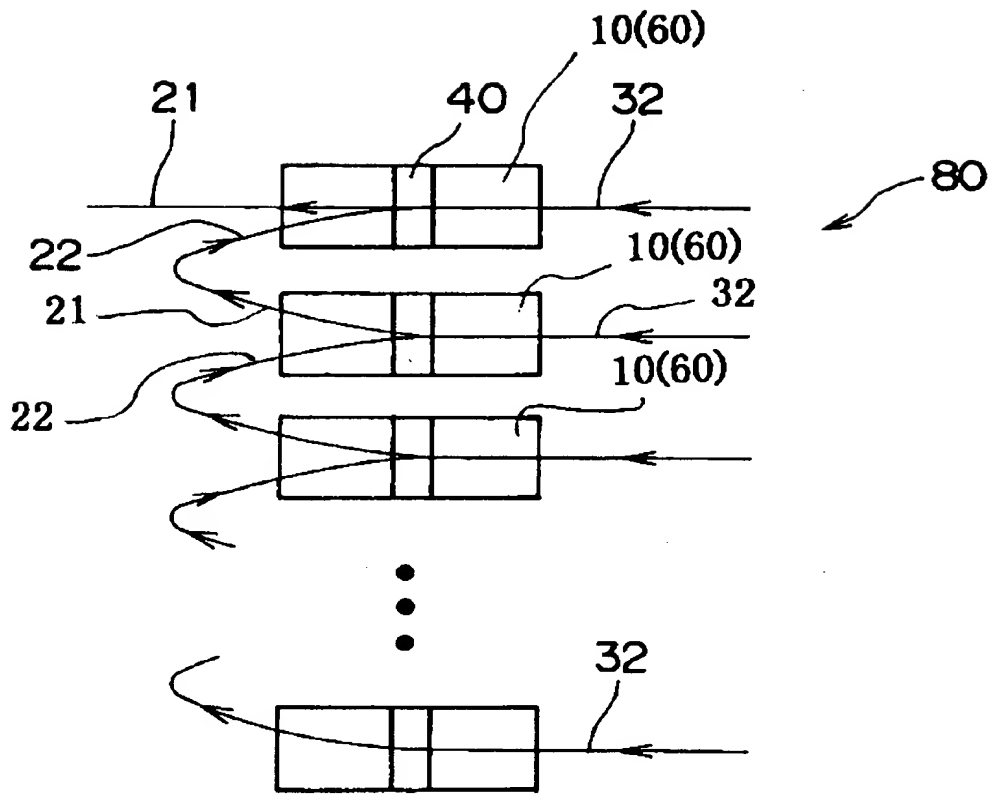


FIG. 9

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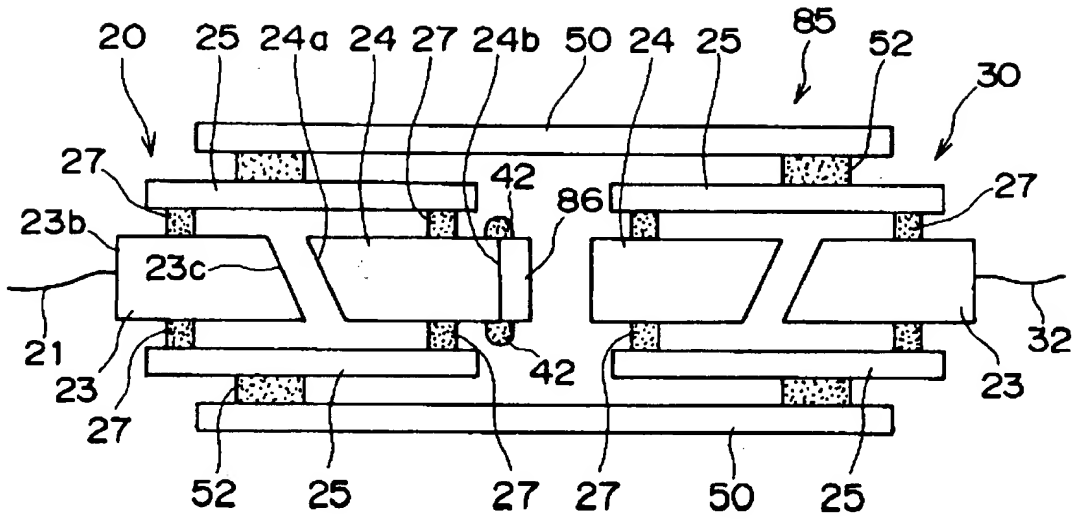


FIG. 10

09901307 070904
T06070 70ET0660

GAIN OF OPTICAL FIBER AMPLIFIER

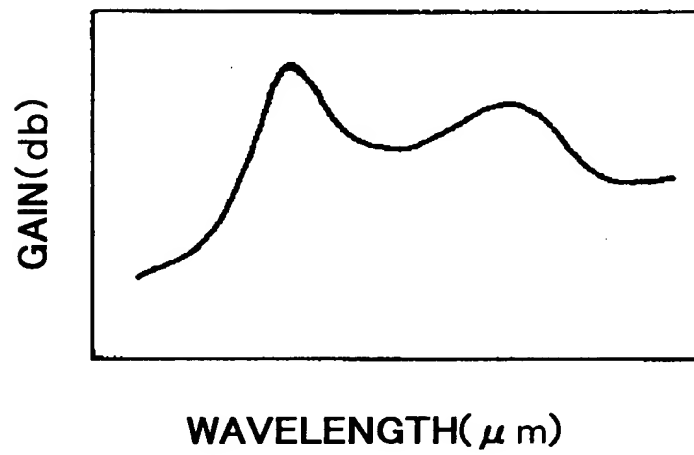
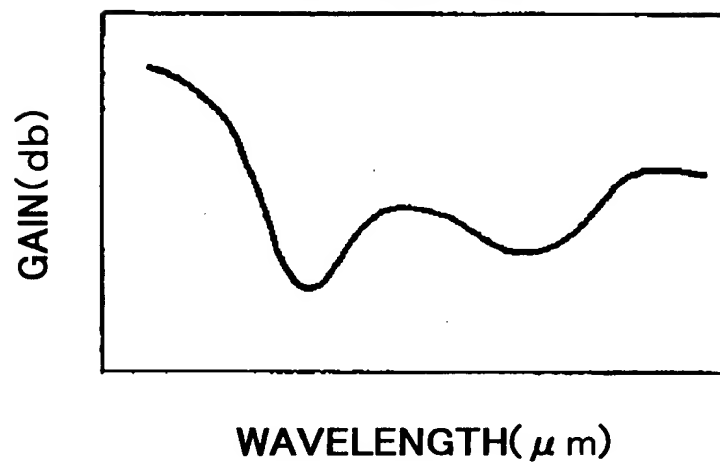


FIG. 11

GAIN OF EQUALIZING FILTER



F I G . 1 2

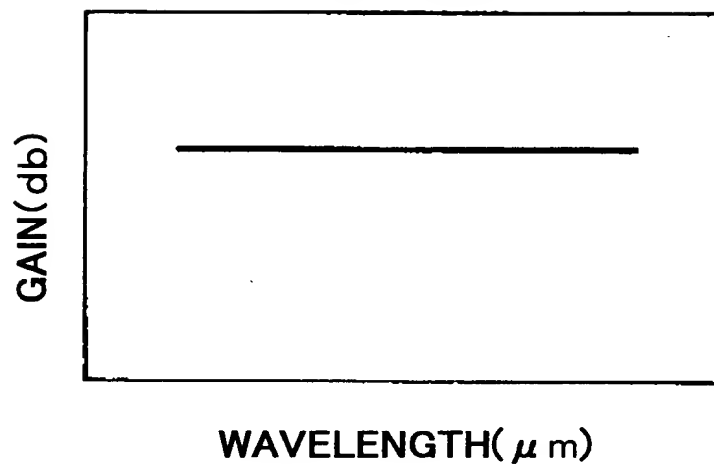
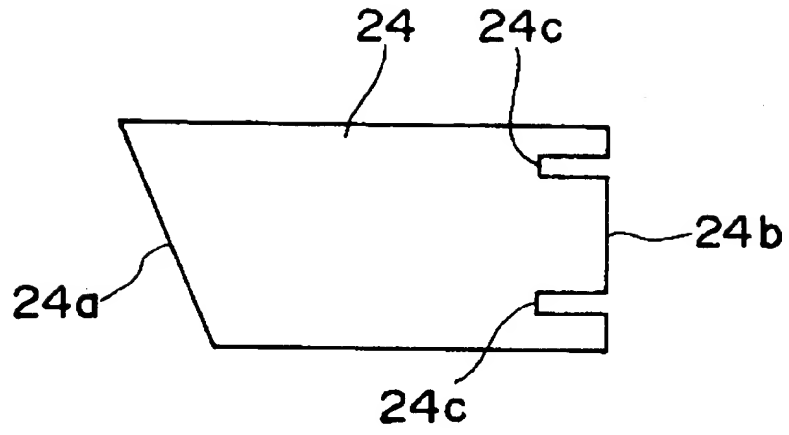


FIG. 13



F I G . 1 4

FIG. 15

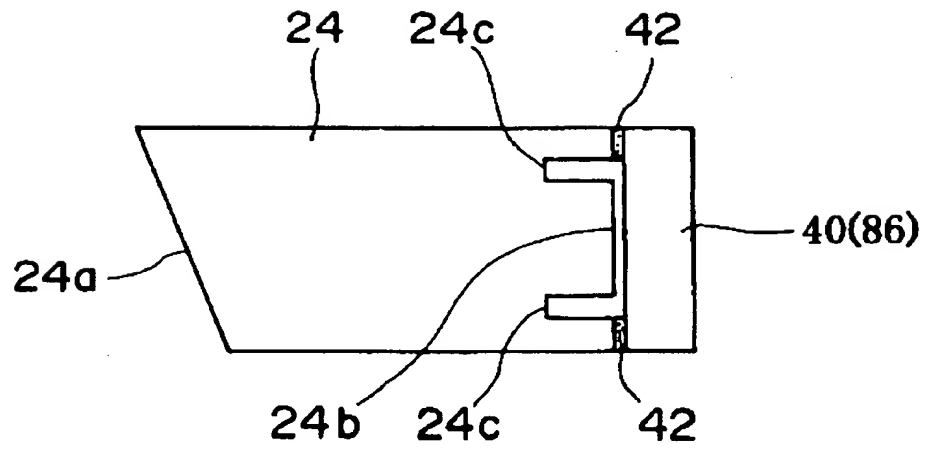


FIG. 15

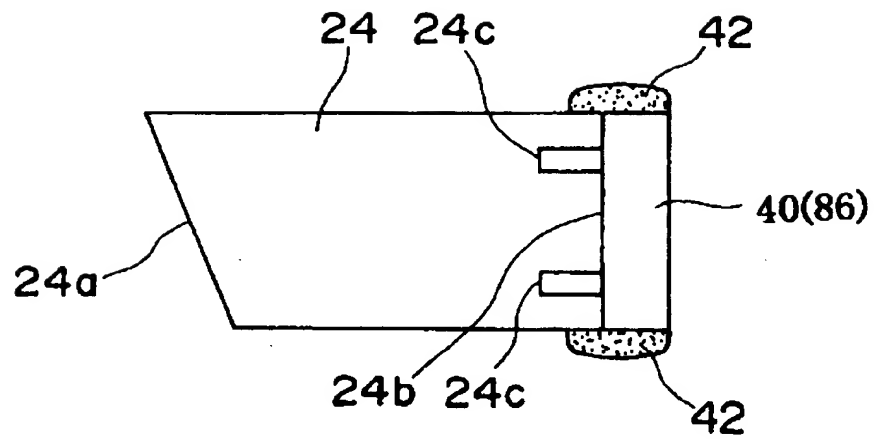


FIG. 16

09901307.070901
T060707/08T0660

Figure 1 is a perspective view of a wedge-shaped member 24. The member has a top surface 24a, a bottom surface 24b, a left side surface 24c, and a right side surface 24d. The right side surface 24d is curved and features a central protrusion 24e.

FIG. 17

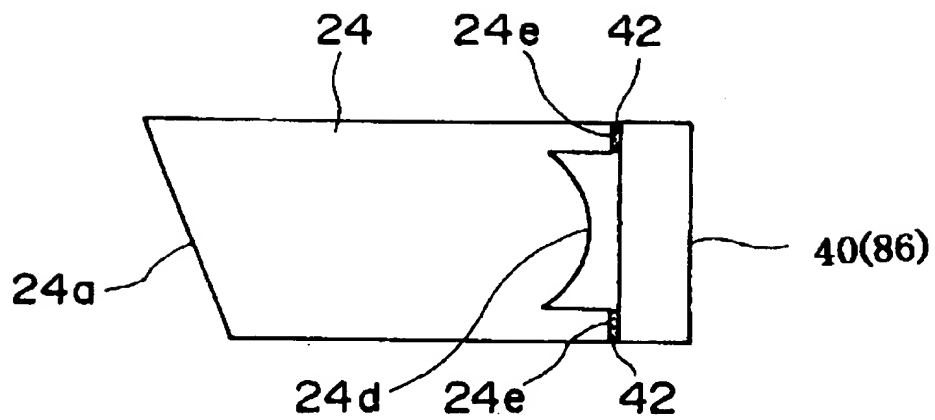


FIG. 18

FIG. 18

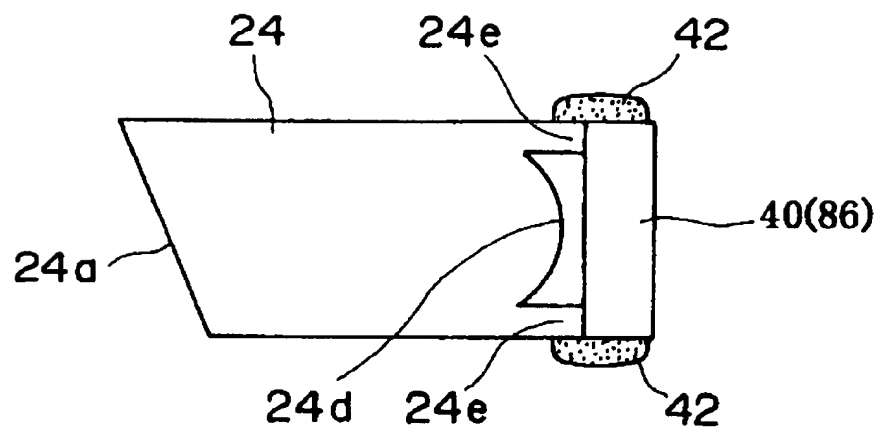


FIG. 19

This cross-sectional view shows two semiconductor devices, 100 and 110, side-by-side. Device 100 on the left has a substrate 101 with a central layer 102. It is surrounded by a stack of layers 103, 104, 105, and 107. A contact 106 is shown on the side of layer 102. Device 110 on the right has a similar structure with a central layer 112 and surrounding layers 113, 114, 115, and 107. A contact 116 is shown on the side of layer 112. Both devices are connected to a common bottom layer 120. A central region 95 is located between the two devices. A label 90 with an arrow points to the right side of the assembly.

FIG. 20